

Title (en)
CHEMICALLY AMPLIFIED PHOTORESIST

Title (de)
CHEMISCH AMPLIFIZIERTER PHOTOLACK

Title (fr)
PHOTORESIST A AMPLIFICATION CHIMIQUE

Publication
EP 0698230 A4 19951024 (EN)

Application
EP 94900495 A 19931029

Priority
• US 9310512 W 19931029
• US 96812092 A 19921029

Abstract (en)
[origin: WO9410608A1] Resists for use in ultraviolet, electron beam and x-ray exposure devices comprising a polymeric or molecular composition the solubility of which is dependent upon the presence of acid removable protecting groups and a sulfonic acid precursor which generates a strong acid upon exposure to such radiation. The preferred sulfonic acid precursors are triflate esters or benzenesulfonyloxy esters of N-hydroxyimides.

IPC 1-7
G03C 5/16; **G03F 7/029**; **G03F 7/004**; **G03F 7/039**

IPC 8 full level
G03F 7/004 (2006.01); **G03F 7/039** (2006.01); **H01L 21/027** (2006.01)

CPC (source: EP)
G03F 7/039 (2013.01)

Citation (search report)
• [X] EP 0445058 A1 19910904 - IBM [US]
• [X] EP 0388343 A2 19900919 - IBM [US]
• See references of WO 9410608A1

Designated contracting state (EPC)
DE FR GB

DOCDB simple family (publication)
WO 9410608 A1 19940511; EP 0698230 A1 19960228; EP 0698230 A4 19951024; JP 2839172 B2 19981216; JP H08501890 A 19960227

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US 9310512 W 19931029; EP 94900495 A 19931029; JP 51139094 A 19931029